

10/728132

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/728132	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:12
L2	1	"6815797".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:09
L3	1	"6563189".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:09
L4	1	"6479382".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L5	1	"6479341".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L6	1	"6252300".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L7	1	"6249136".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L8	1	"6221769".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L9	1	"6187677".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L10	1	"6110825".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L11	1	"6027964".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:10
L12	1	"6015726".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L13	1	"6010951".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L14	1	"5904529".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L15	1	"5872053".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L16	1	"5739067".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L17	1	"5702976".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L18	1	"5674787".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:11
L19	1	"5627106".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:12

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L20	1	"5608237".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:12
L21	1	"5530552".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:12
L22	2	("6525375").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:38
L23	1	"6245615".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:25
L24	1	"6281547".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:25
L25	1	"5828101".PN.	USPAT; USOCR	OR	OFF	2006/12/15 12:26
L26	2	("6639301").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:38
L27	0	EPROM and floating and gate and control and source and drain and region and n-type and p-type and polysilicon and electrode and conductivity and trench and transistor and (crystallographic adj orientation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:41
L28	16	EPROM and floating and gate and control and source and drain and region and n-type and p-type and polysilicon and electrode and conductivity and trench and transistor and (crystallographic adj orientation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:43
L29	17	EPROM and floating and gate and control and source and drain and region and n-type and p-type and polysilicon and electrode and conductivity and trench and transistor and channel and negative and positive and voltage and band and (tunnel adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:45
L30	53	EPROM and floating and gate and control and source and drain and region and n-type and p-type and polysilicon and electrode and conductivity and trench and transistor and channel and (tunnel adj oxide) and dop\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/15 12:46